

204612US-2



#9/a
9/4/2
Sunder

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

YUUCHI HIRANO ET AL.

: EXAMINER: THIEN F. TRAN

SERIAL NO: 09/802,886

:

FILED: MARCH 12, 2001

: GROUP ART UNIT: 2811

FOR: SEMICONDUCTOR DEVICE AND
METHOD OF MANUFACTURING THE SAME

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated June 6, 2002, please enter the following
Amendment and consider the following Remarks:

IN THE CLAIMS

*Please amend the claims as shown in the Attachment, in which underlining and
bracketing show the changes introduced into the previously-pending claims to arrive at the clean
claims provided below:*

- Sub
B1
C1
1. (Amended) A semiconductor device comprising:
an SOI substrate having a structure in which a semiconductor substrate, an insulating
layer and a semiconductor layer are layered in this order;
a partial-isolation insulating film formed in a main surface of said semiconductor layer.

RECEIVED
AUG 30 2002
TECHNOLOGY CENTER 2800